

# O(n) Layout-Coloring for Multiple-Patterning Lithography and Conflict-Removal Using Compaction

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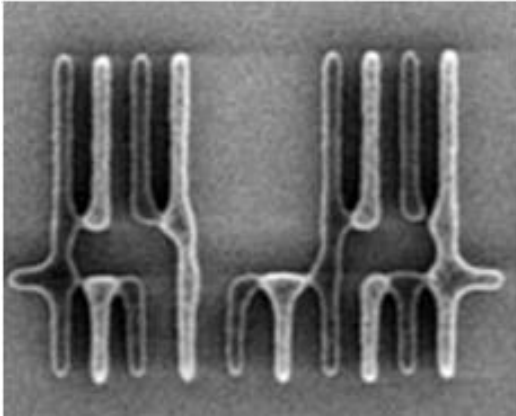
EE Dept, **NanoCAD Lab**<sup>\*</sup>



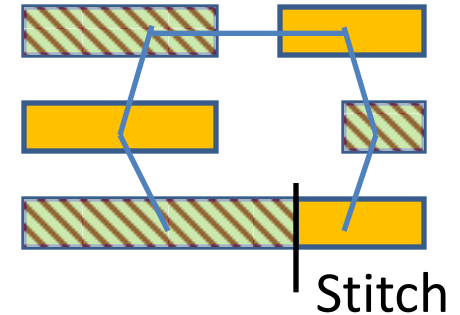
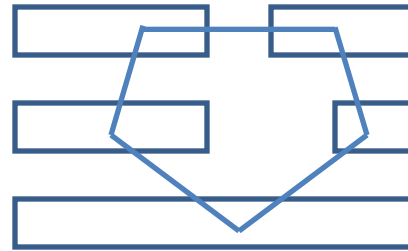
Austin Research Lab<sup>†</sup>  
San Jose<sup>‡</sup>

Semiconductor R&D Center<sup>§</sup>

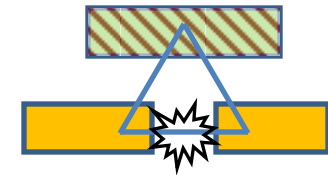
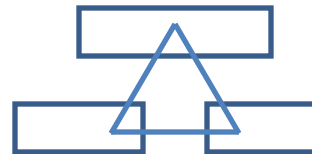
# Multiple-Patterning Lithography



C. Mack, IEEE Spectrum 08

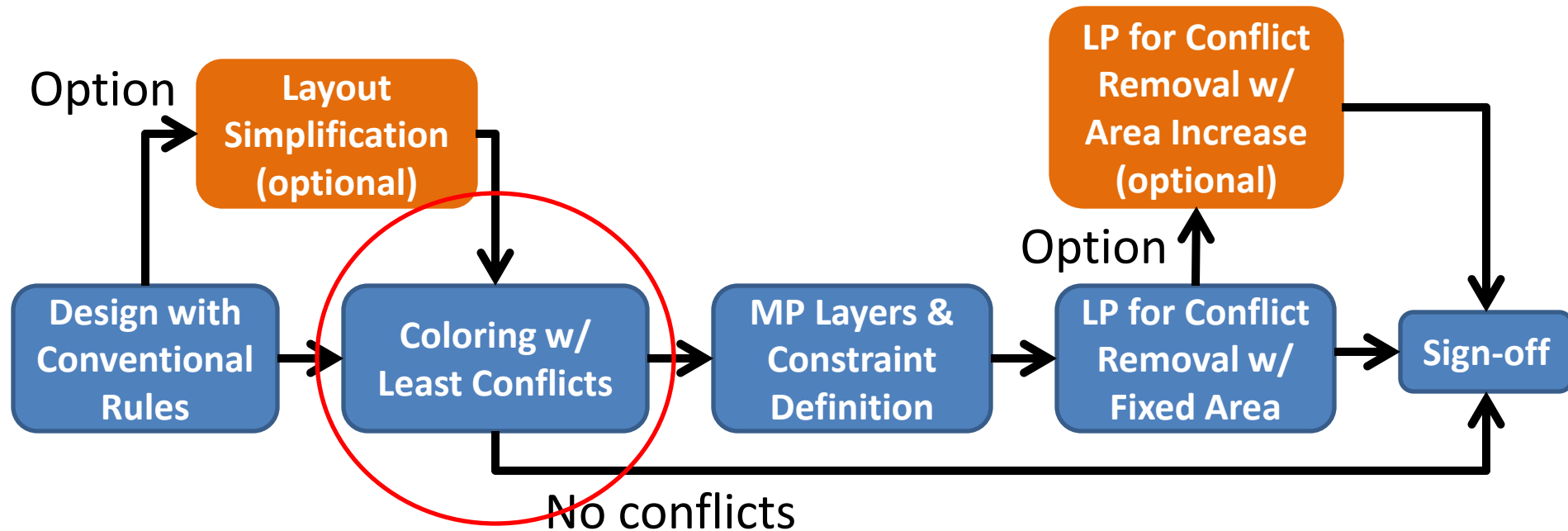


*Native conflict* → *needs layout change*



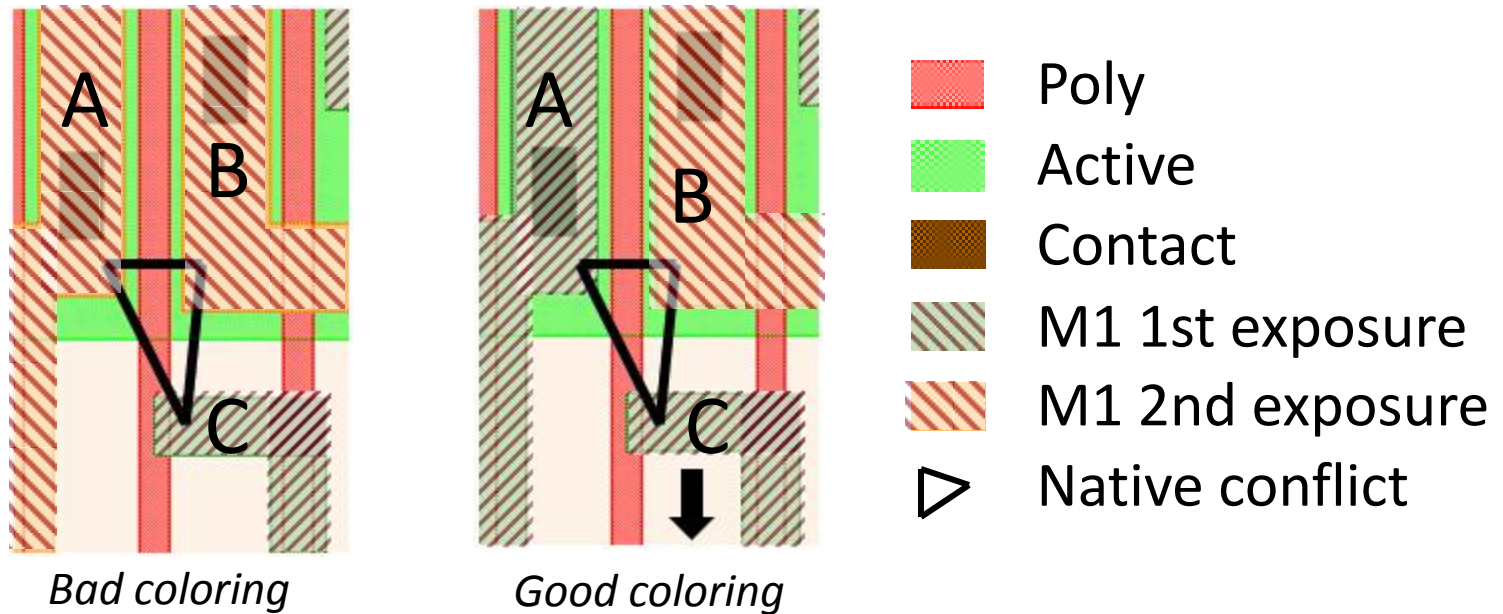
- Delays in EUV → MP is inevitable for sub 20nm tech
  - DP/TP in LELE, SADP
- Biggest challenge is coloring conflicts
- E.g., DP in LELE process

# Overview of the Framework



- Fast linear time coloring
- LP-based compaction for conflict removal
  - Simultaneously fixes all conflicts without creating new conflicts

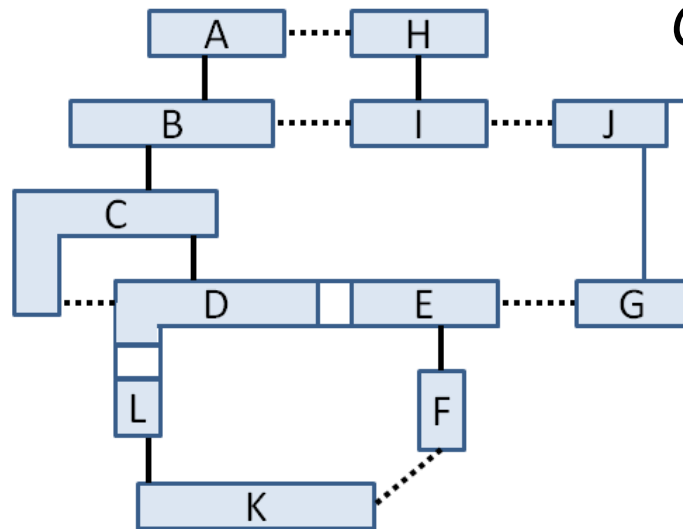
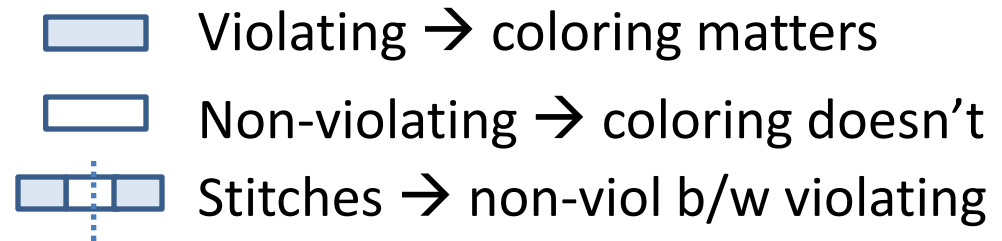
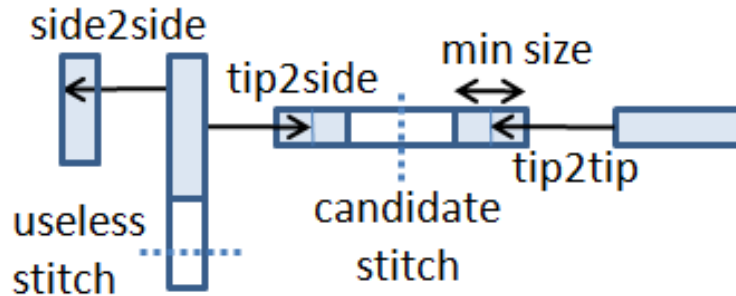
# Preferred Coloring



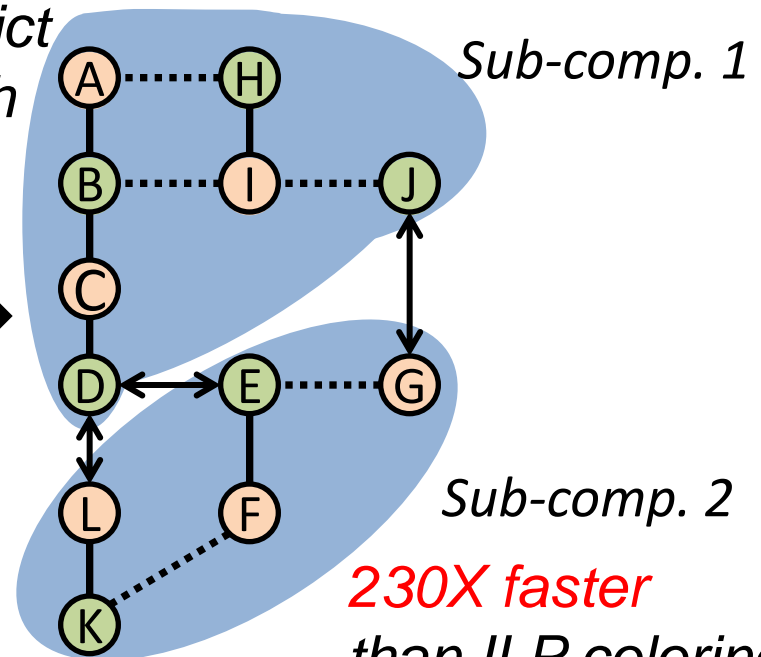
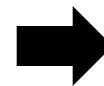
- Coloring of native conflicts affects efficiency of conflict removal
- Give preference for opposite coloring for certain violations over others → label violations critical vs. less-critical
  - E.g., horizontal spacing violation more critical than vertical or diagonal in case of vertical poly orientation

# O(n) Coloring

## Projection

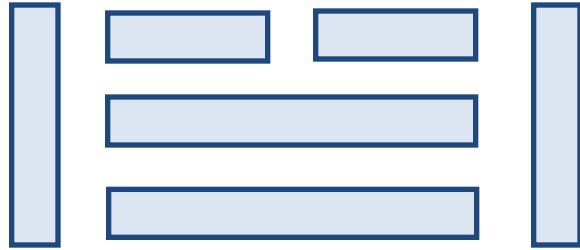


## Conflict Graph



**230X faster**  
than ILP coloring <sup>5</sup>

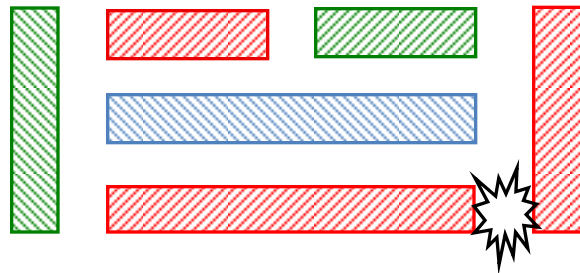
# Triple Patterning – Extending 2-Coloring to 3-Coloring



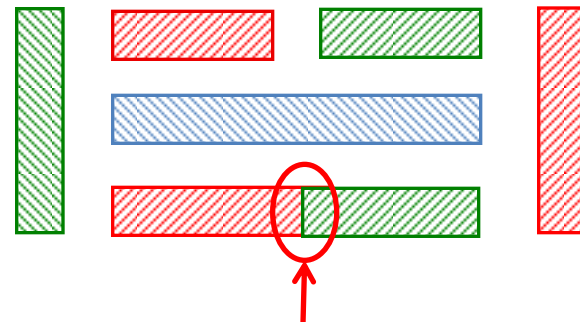
*Projection*  $\rightarrow$  all parts violating  $\rightarrow$  no stitches

*No 3-Coloring Solution!*

*Valid coloring not possible*



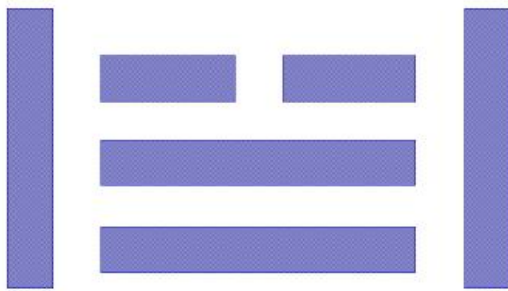
*Valid coloring with TP stitch*



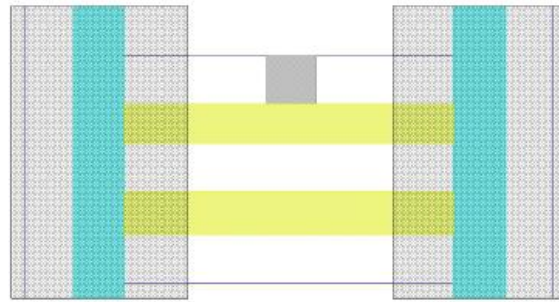
*Unseen candidate stitch*

- Common 2-coloring cannot be extended to 3-coloring
  - 3-coloring stitches can be *almost anywhere!*

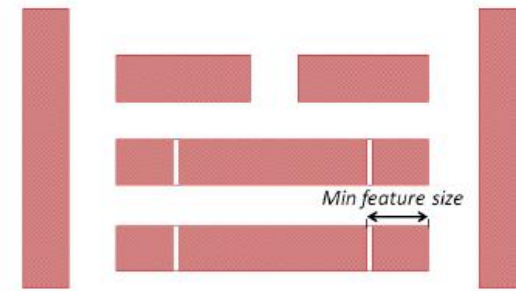
# TP Coloring Example



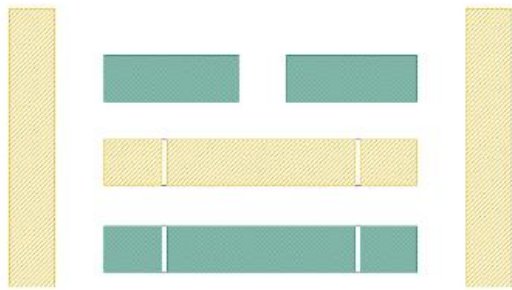
(a): Layout



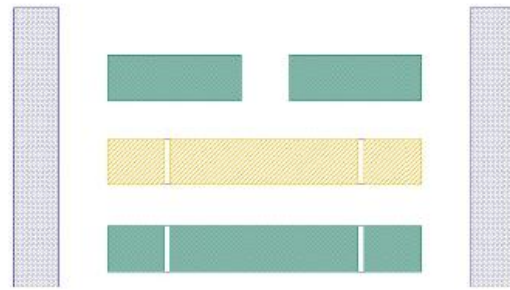
(b): Projection



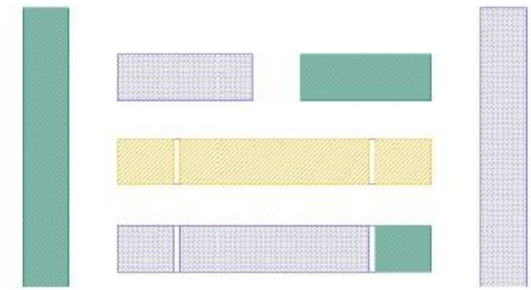
(c): Violating parts



(d): C0/C1 coloring



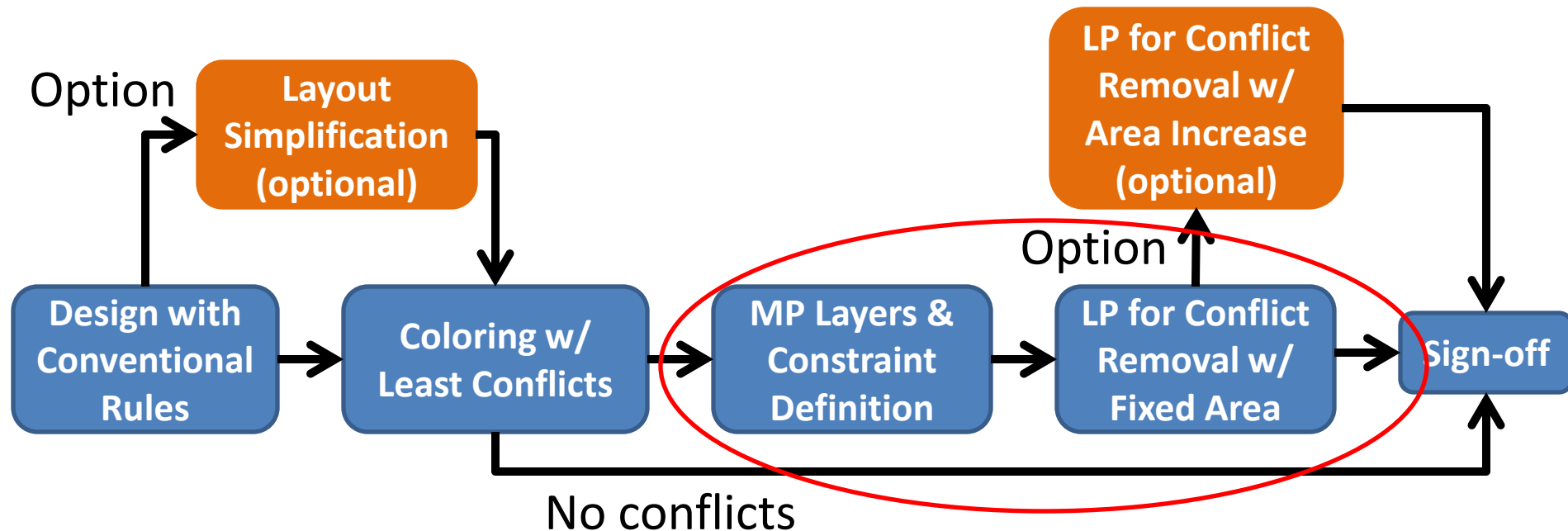
(e): C0/C2 coloring



(f): C1/C2 coloring

- Leverage TP Stitch Capability → Stitch at S2S violating parts
- Color violating parts w/ C0/C1-C0/C2-C1/C2 coloring cycle
  - Use existing infrastructure of DP coloring
- Works well but not for complex layouts → simplifications needed

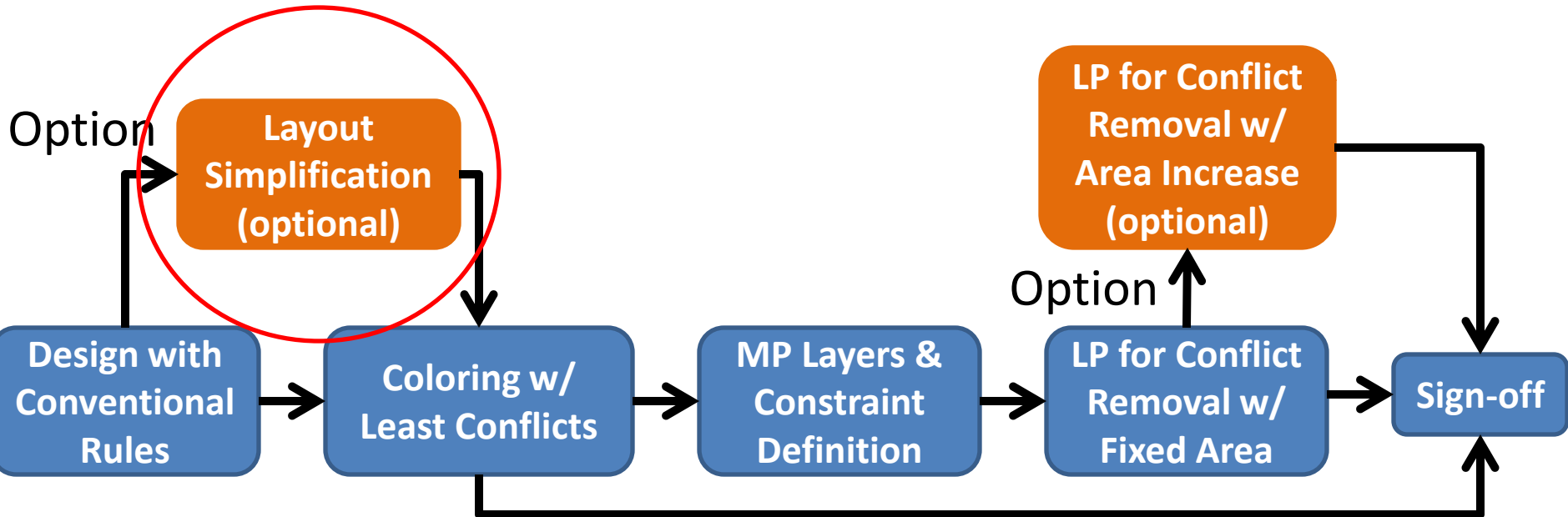
# Conflict-Removal Using Compaction



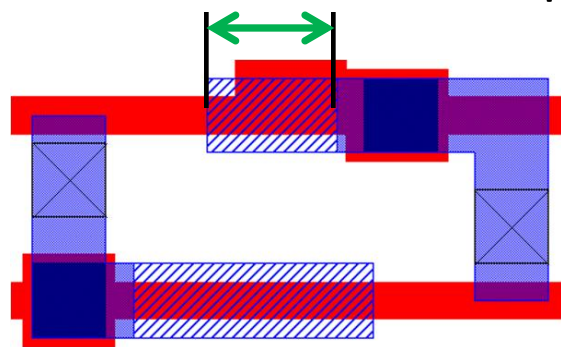
- Color → define DRs between DP layers (e.g., M1A/M1B)
  - Same-color spacing, ≠ color spacing, M1A/M1B overlap
  - Overhang rules with top/bottom layers (union M1A M1B)
- Compaction → Full legalization across all layers concurrently



# Sacrificing Unnecessary Layout Features

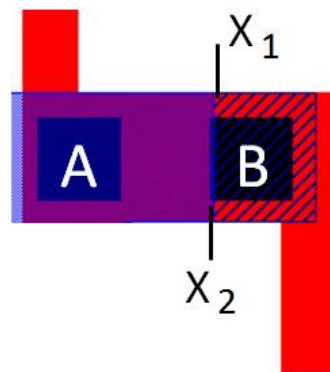


*Recommended rule*



Pin Segments

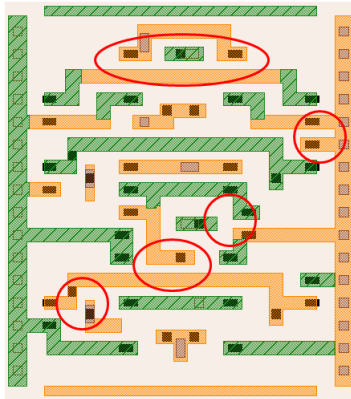
No conflicts



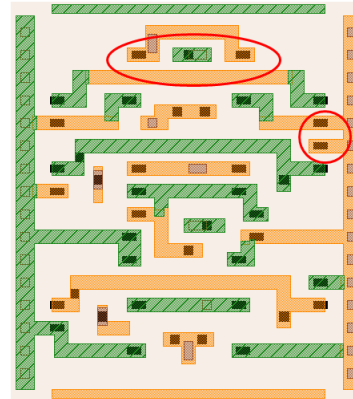
Redundant Contacts

- Poly
- New M1
- ▨ Removed M1
- ⊠ Via 1
- $X_1$  New M1 edge  $x$  location
- $X_2$  Contact edge  $x$  location

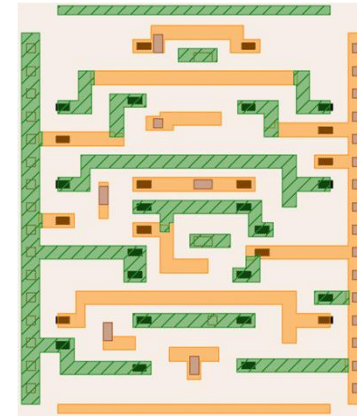
# Conflict Removal Results



Original  
5 conflicts



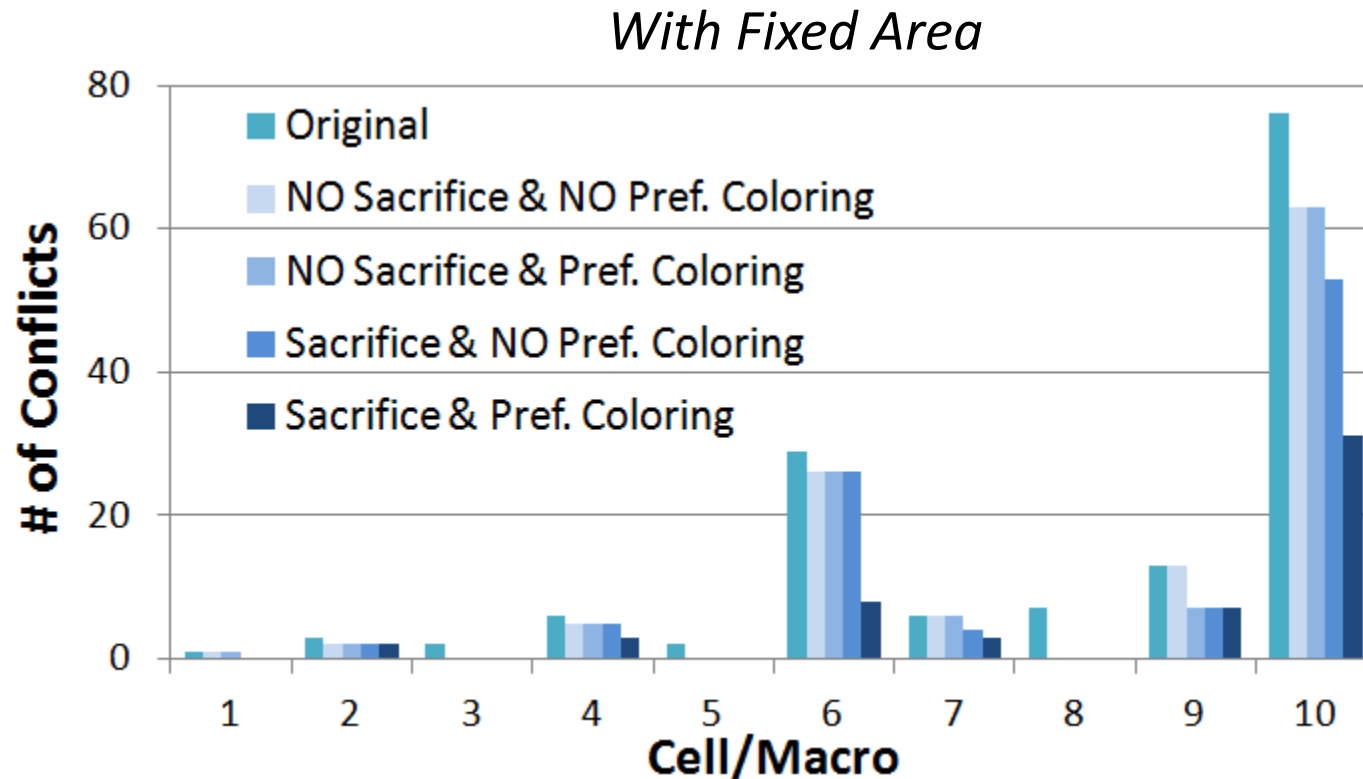
Same area,  
2 conflicts



No conflicts, 6.2% area  
increase

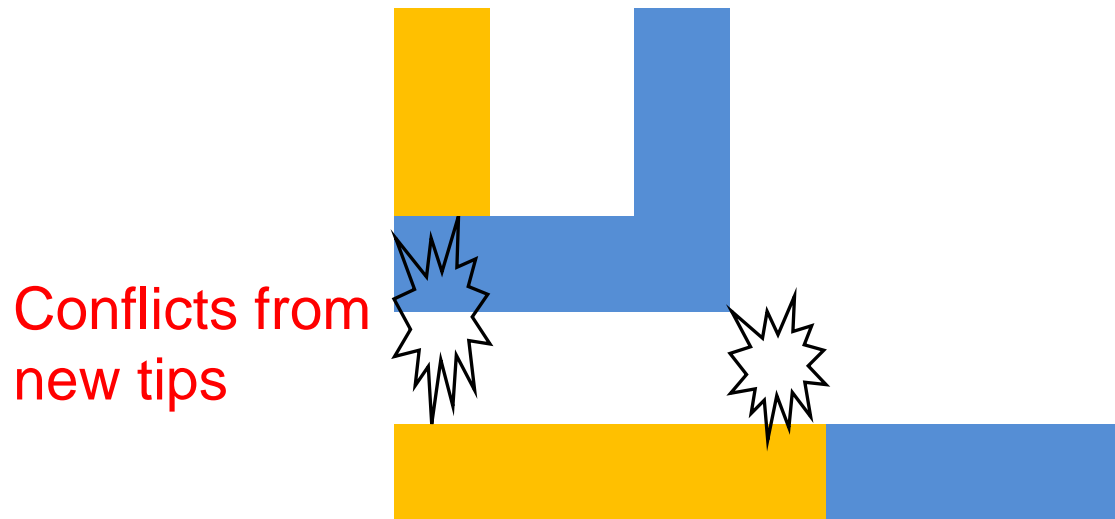
- DP-compatible cells
  - No area overhead for simple cells
  - Modest area overhead (at most 9%) for complex cells and macros
  - Few sacrificed redundant contacts (CA)
- Less than 1 min in real time for largest macro (460 trans.)

# Effects of Sacrifice and Preferred Coloring



- Need both enhancement methods
- If enhancements not applied → 2X more conflicts in final layout

# Final Notes



- Problems with Newly Created Tips
  - One way → use pessimistic projection → non-optimal
  - Less of a problem when using compaction-based legalization
- Methodology applicable for SADP, only need
  - A layout-coloring method
  - A set of design rules for SADP-compatible layout

**Thank you**

Questions during poster session